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2N4400

MMBT4400





NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 500 mA.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	6.0	V
I _C	Collector Current - Continuous	600	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic Max		lax	Units	
		2N4400	*MMBT4400		
P_D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/∘C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W	

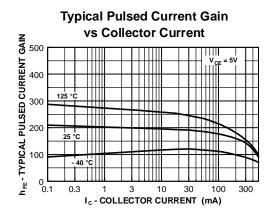
NPN General Purpose Amplifier (continued)

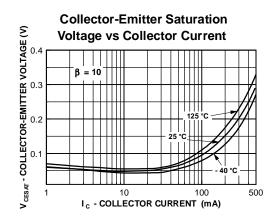
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	6.0		V
I _{CEX}	Collector Cutoff Current	$V_{CE} = 35 \text{ V}, \ V_{EB} = 0.4 \text{ V}$		0.1	μΑ
I _{BL}	Emitter Cutoff Current	$V_{CE} = 35 \text{ V}, \ V_{EB} = 0.4 \text{ V}$		0.1	μΑ
ON CHAF	RACTERISTICS*				
h _{FE}	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	20		
		$V_{CE} = 1.0 \text{ V}, I_{C} = 10 \text{ mA}$	40		
		$V_{CE} = 1.0 \text{ V}, I_{C} = 150 \text{ mA}$	50	150	
\/	Collector-Emitter Saturation Voltage	$V_{CE} = 2.0 \text{ V}, I_{C} = 500 \text{ mA}$ $I_{C} = 150 \text{ mA}, I_{B} = 15 \text{ mA}$	20	0.40	V
V _{CE(sat)}	Collector-Entitler Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.40	V
V	Base-Emitter Saturation Voltage		0.75		
v BE(Sat)	Dase-Limiter Saturation Voltage	$I_{\rm C} = 150 \text{ mA}, I_{\rm B} = 15 \text{ mA}$	0.75	0.95	V
v BE(sat)	Base-Efficier Sacuration voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	0.75	0.95 1.2	V
v BE(sat)	base-Emilier Saturation voltage		0.75		
	SIGNAL CHARACTERISTICS		0.75		1
SMALL S			0.75		1
SMALL S Cob Cib	SIGNAL CHARACTERISTICS	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	0.75	1.2	V
SMALL S C _{ob} C _{ib}	SIGNAL CHARACTERISTICS Output Capacitance	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$	2.0	6.5	V V
SMALL S C _{ob} C _{ib}	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance	$\begin{split} &I_{C} = 500 \text{ mA}, \ I_{B} = 50 \text{ mA} \\ \\ &V_{CB} = 5.0 \text{ V}, \ f = 140 \text{ kHz} \\ \\ &V_{EB} = 0.5 \text{ V}, \ f = 140 \text{ kHz} \\ \\ &I_{C} = 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \end{split}$		6.5	V V
SMALL S C _{ob} C _{ib} h _{fe}	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain	$\begin{split} &I_{C} = 500 \text{ mA}, \ I_{B} = 50 \text{ mA} \\ \\ &V_{CB} = 5.0 \text{ V}, \ f = 140 \text{ kHz} \\ \\ &V_{EB} = 0.5 \text{ V}, \ f = 140 \text{ kHz} \\ \\ &I_{C} = 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ &f = 100 \text{ MHz} \end{split}$	2.0	6.5	V V
SMALL S C _{ob} C _{ib} h _{fe} h _{fe}	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain	$\begin{split} &I_C = 500 \text{ mA}, \ I_B = 50 \text{ mA} \\ &V_{CB} = 5.0 \text{ V}, \ f = 140 \text{ kHz} \\ &V_{EB} = 0.5 \text{ V}, \ f = 140 \text{ kHz} \\ &I_C = 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 10 \text{ V}, \ I_C = 1.0 \text{ mA}, \end{split}$	2.0	6.5 30 250	PF pF KΩ
SMALL S	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance	$\begin{split} &I_C = 500 \text{ mA}, \ I_B = 50 \text{ mA} \\ &V_{CB} = 5.0 \text{ V}, \ f = 140 \text{ kHz} \\ &V_{EB} = 0.5 \text{ V}, \ f = 140 \text{ kHz} \\ &I_C = 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 10 \text{ V}, \ I_C = 1.0 \text{ mA}, \end{split}$	2.0 20 0.5	6.5 30 250 7.5	pF pF
SMALL S Cob Cib hfe hfe hie hre	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio	$\begin{split} &I_C = 500 \text{ mA}, \ I_B = 50 \text{ mA} \\ &V_{CB} = 5.0 \text{ V}, \ f = 140 \text{ kHz} \\ &V_{EB} = 0.5 \text{ V}, \ f = 140 \text{ kHz} \\ &I_C = 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 10 \text{ V}, \ I_C = 1.0 \text{ mA}, \end{split}$	2.0 20 0.5 0.1	1.2 6.5 30 250 7.5 8.0	PF PF ΚΩ x 10 ⁻⁴
SMALL S Cob Cib hfe hie hoe	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio	$\begin{split} &I_C = 500 \text{ mA}, \ I_B = 50 \text{ mA} \\ &V_{CB} = 5.0 \text{ V}, \ f = 140 \text{ kHz} \\ &V_{EB} = 0.5 \text{ V}, \ f = 140 \text{ kHz} \\ &I_C = 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 10 \text{ V}, \ I_C = 1.0 \text{ mA}, \end{split}$	2.0 20 0.5 0.1	1.2 6.5 30 250 7.5 8.0	PF PF KΩ x 10 ⁻⁴
SMALL S Cob Cib hfe hfe hie hre hoe	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio Output Admittance	$\begin{split} &I_C = 500 \text{ mA}, \ I_B = 50 \text{ mA} \\ &V_{CB} = 5.0 \text{ V}, \ f = 140 \text{ kHz} \\ &V_{EB} = 0.5 \text{ V}, \ f = 140 \text{ kHz} \\ &I_C = 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 10 \text{ V}, \ I_C = 1.0 \text{ mA}, \end{split}$	2.0 20 0.5 0.1	1.2 6.5 30 250 7.5 8.0	PF PF ΚΩ x 10 ⁻⁴
SMALL S Cob Cib hfe hie hre hoe	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio Output Admittance	$I_{C} = 500 \text{ mA}, I_{B} = 50 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V}, I_{C} = 1.0 \text{ mA},$ $f = 1.0 \text{ kHz}$	2.0 20 0.5 0.1	1.2 6.5 30 250 7.5 8.0 30	PF pF KΩ x 10 ⁻⁴ μmhos
SMALL S Cob Cib hfe hie hoe	Output Capacitance Input Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio Output Admittance NG CHARACTERISTICS Delay Time	$\begin{split} I_C &= 500 \text{ mA}, \ I_B = 50 \text{ mA} \\ \\ V_{CB} &= 5.0 \text{ V}, \ f = 140 \text{ kHz} \\ \\ V_{EB} &= 0.5 \text{ V}, \ f = 140 \text{ kHz} \\ \\ I_C &= 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CE} &= 10 \text{ V}, \ I_C = 1.0 \text{ mA}, \\ f &= 1.0 \text{ kHz} \\ \\ \\ V_{CC} &= 30 \text{ V}, \ I_C = 150 \text{ mA}, \end{split}$	2.0 20 0.5 0.1	1.2 6.5 30 250 7.5 8.0 30	PF pF RΩ x 10 ⁻⁴ μmhos

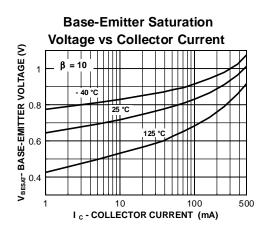
^{*}Pulse Test: Pulse Width £ 300 ms, Duty Cycle £ 2.0%

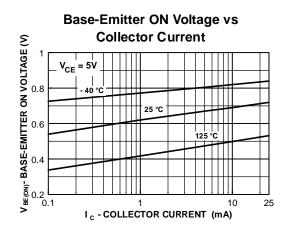
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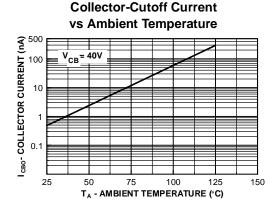
Typical Characteristics

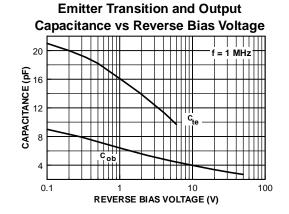








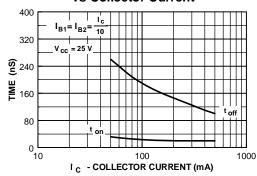




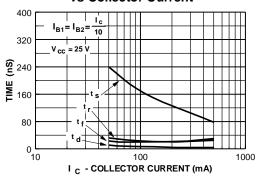
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Typical Characteristics (continued)

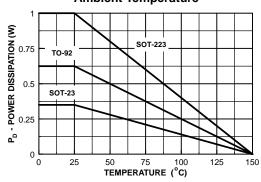
Turn On and Turn Off Times vs Collector Current



Switching Times vs Collector Current

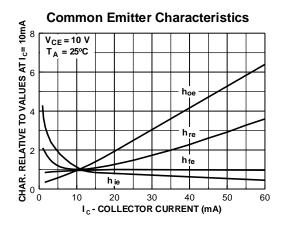


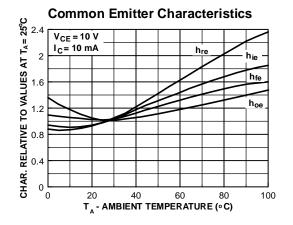
Power Dissipation vs Ambient Temperature

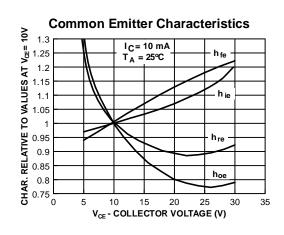


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Typical Common Emitter Characteristics (f = 1.0kHz)







(continued)

Test Circuits

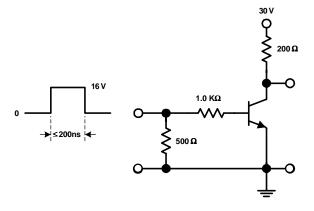


FIGURE 1: Saturated Turn-On Switching Timer

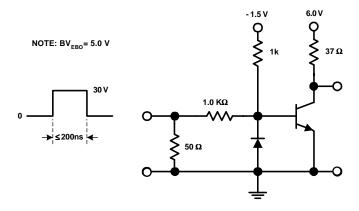


FIGURE 2: Saturated Turn-Off Switching Time

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